

## Chip Specification

### General Description:

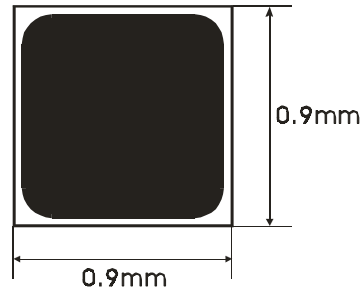
Schottky Diode chips with Mo-barrier for switch mode power rectifiers with the following features:

- \* **Guard-ring for stress protection**
- \* **Extremely low forward voltage**
- \* **125 °C operation junction temperature**
- \* **reverse avalanche behavior**

### Mechanical Data:

#### SB 1XX passivated Silicon Chip

Dimension(mm)	0.9x0.9
Thickness:	350 +- 20 $\mu$ m
Metallization:	
Top ( Anode ) :	Al Ag
Bottom ( Cathode ) :	TiNiAg



Forward Current(A)	1 A
Reverse Voltage (V):	23, 43, 100 V

Type	Chip	$V_R(V)$	$V_F(V)$ @25 C	$I_{RM}$ @ $V_{RMM}$
	size(mm)		at $I_f=1A$	at 25 C
SB120	0.9x0.9	23V	400mV	0,5mA
SB140	0.9x0.9	43 V	500mV	0,5mA
SB1100	0.9x0.9	100 V	730mV	0,5mA

Note: Other voltages,  $V_f$  & Top Metal AL are available

